N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[d]	Q_g (Typ.)
40	0.0033 at V_{GS} = 10 V	90	87
	0.0041 at V_{GS} = 4.5 V	90	

FEATURES

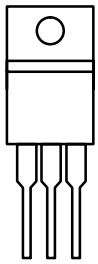
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

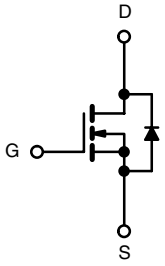
- Power Supply
  - Secondary Synchronous Rectification
- DC/DC Converter

TO-220AB



Top View

Ordering Information: SUP90N04-3m3P-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	90[d]	A
	T_C = 70 °C		90[d]	
Pulsed Drain Current		I_{DM}	160	
Avalanche Current		I_{AS}	60	
Single Avalanche Energy[a]	L = 0.1 mH	E_{AS}	180	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	125[b]	W
	T_A = 25 °C[c]		3.1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	1	

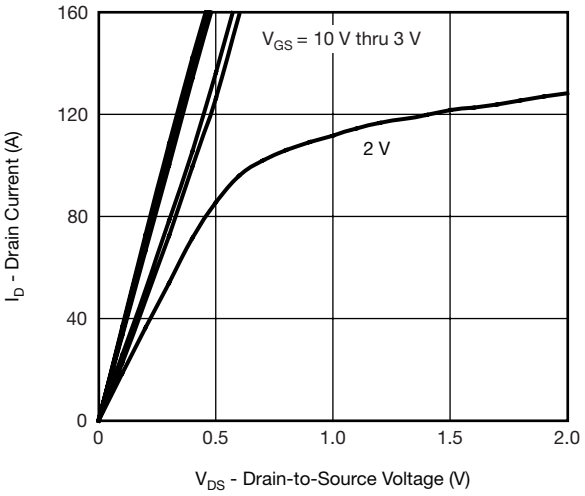
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When Mounted on 1" square PCB (FR-4 material).
d. Package limited.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} = 0 V, I_D = 250 µA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			1	µA
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 150 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	50			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 22 A		0.0027	0.0033	Ω
		V_{GS} = 4.5 V, I_D = 20 A		0.0034	0.0041	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		169		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz		5286		pF
Output Capacitance	C_{oss}			705		
Reverse Transfer Capacitance	C_{rss}			283		
Total Gate Charge[c]	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 20 A		87	131	nC
Gate-Source Charge[c]	Q_{gs}			15.3		
Gate-Drain Charge[c]	Q_{gd}			12.2		
Gate Resistance	R_g	f = 1 MHz	0.5	2.7	5.4	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 2 Ω I_D ≅ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		11	20	ns
Rise Time[c]	t_r			7	14	
Turn-Off Delay Time[c]	$t_{d(off)}$			45	68	
Fall Time[c]	t_f			7	14	
Drain-Source Body Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				90	A
Pulsed Current	I_{SM}				160	
Forward Voltage[a]	V_{SD}	I_F = 10 A, V_{GS} = 0 V		0.72	1.2	V
Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/µs		42	63	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2.5	3.8	A
Reverse Recovery Charge	Q_{rr}			52	78	nC

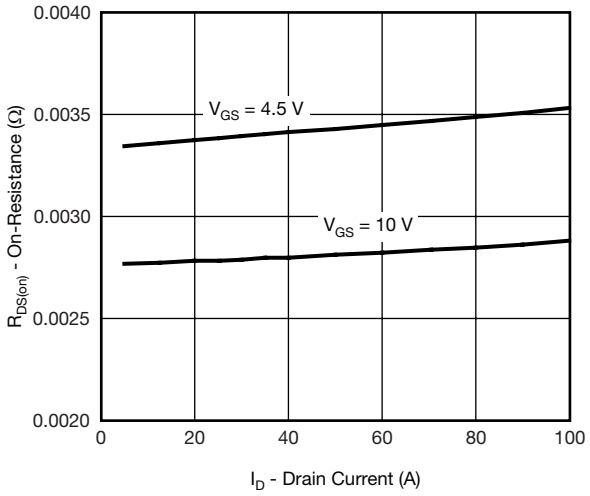
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

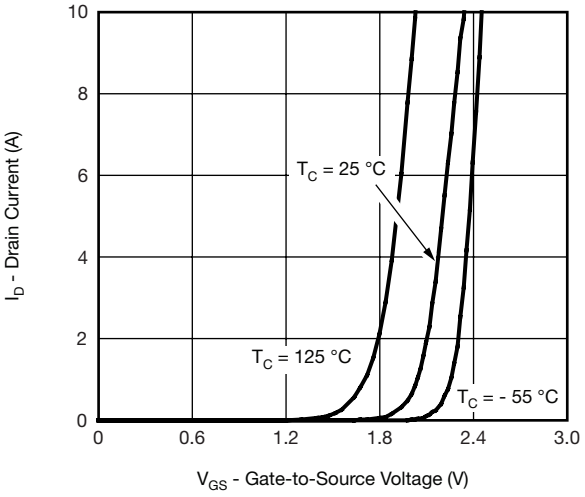
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



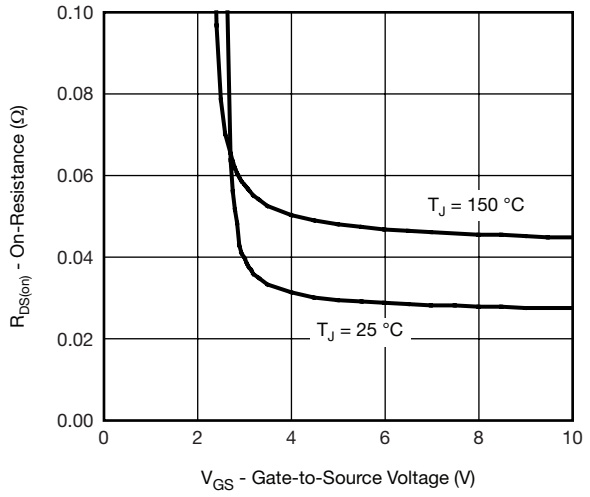
Output Characteristics



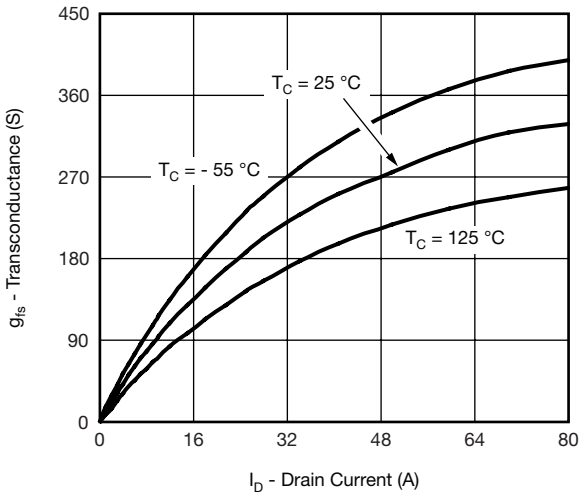
On-Resistance vs. Drain Current



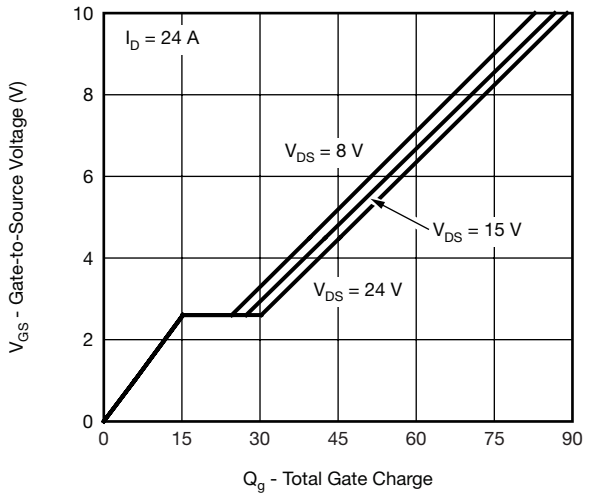
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

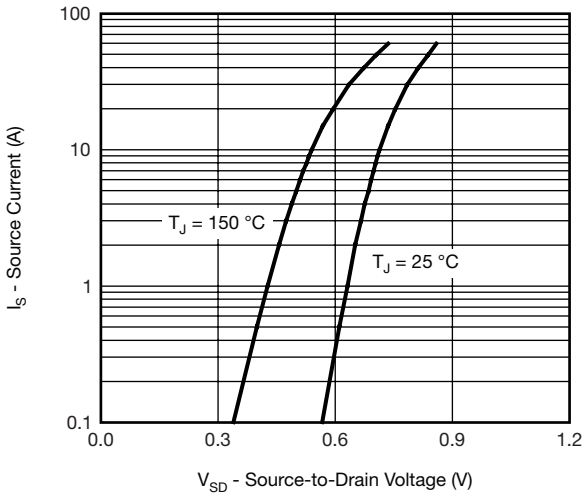


Transconductance

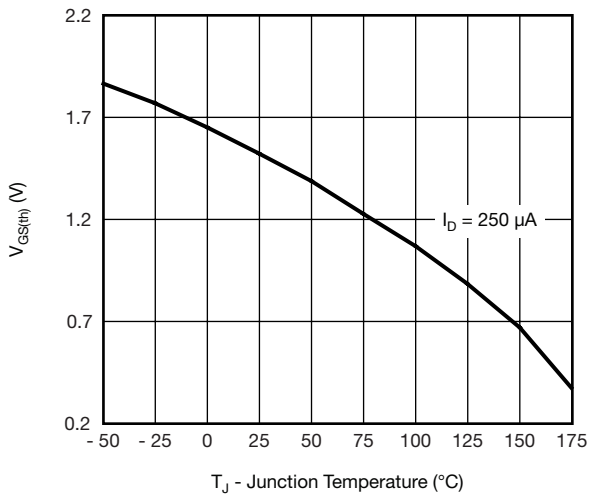


Gate Charge

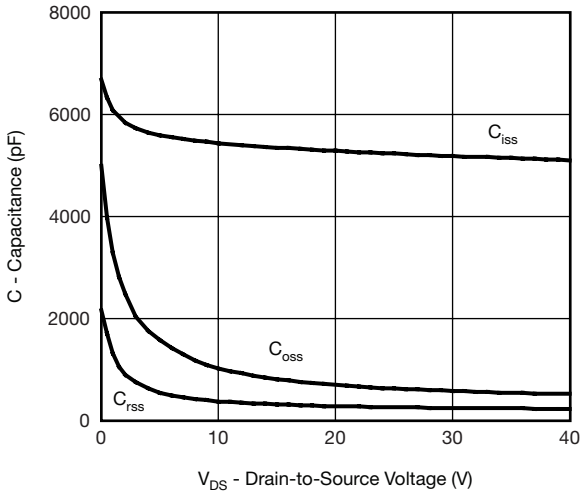
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



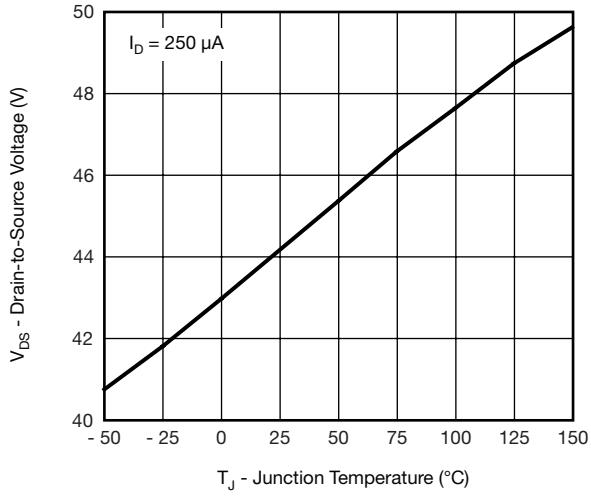
Source-Drain Diode Forward Voltage



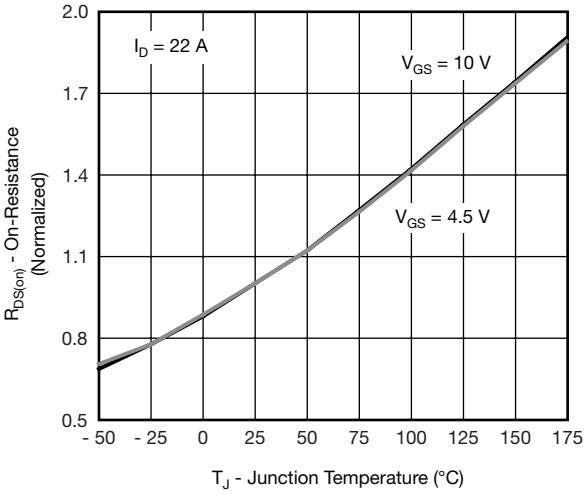
Threshold Voltage



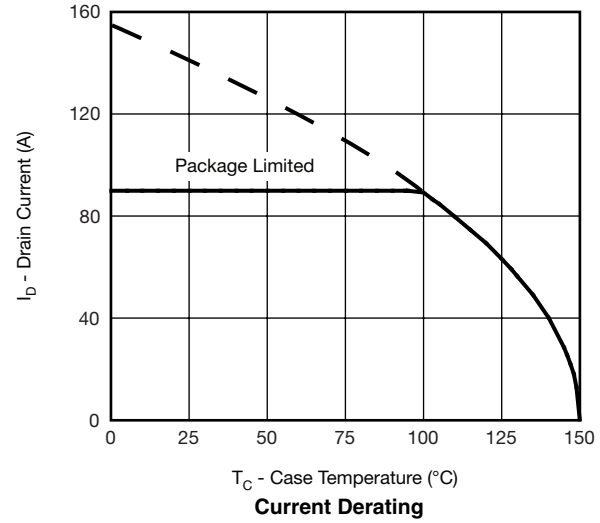
Capacitance



Drain Source Breakdown vs. Junction Temperature

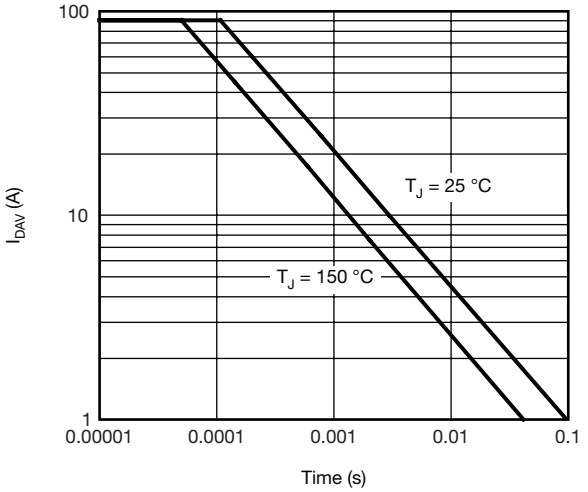


On-Resistance vs. Junction Temperature

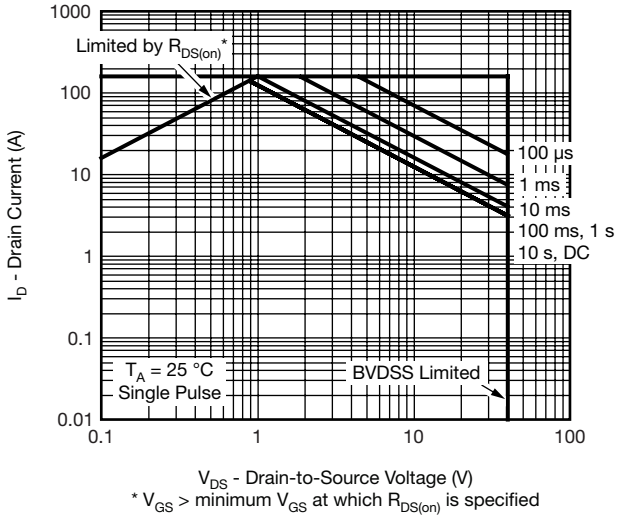


Current Derating

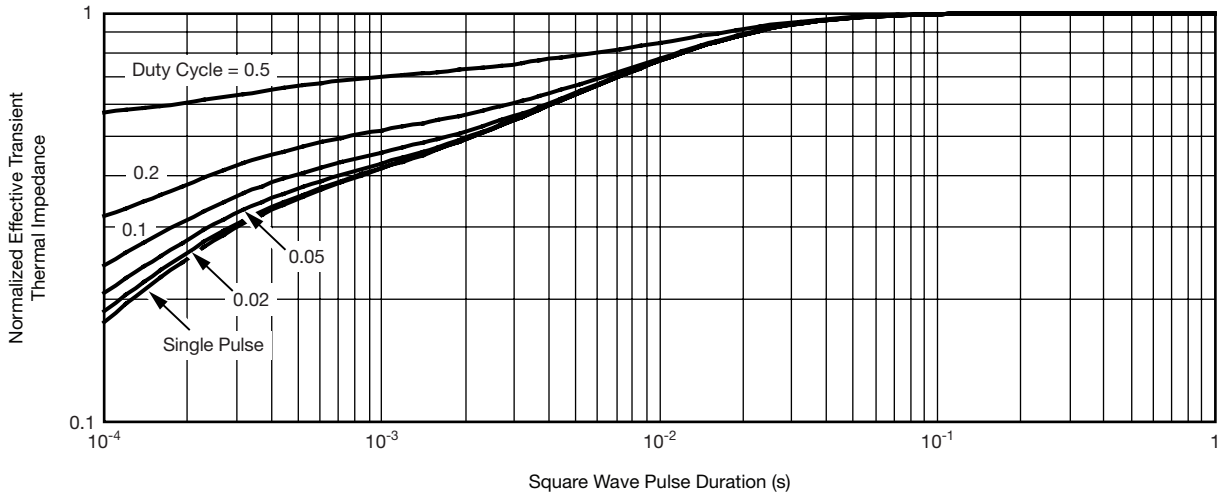
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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